Hiroshi Yamaguchi

List of Publications by Year
in descending order

320	7,129	87888 38	82547 72
papers	citations	h-index	g-index

327	327	327	4895
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Low-Temperature Growth of GaAs and AlAs-GaAs Quantum-Well Layers by Modified Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1986, 25, L868-L870.	1.5	369
2	Migration-Enhanced Epitaxy of GaAs and AlGaAs. Japanese Journal of Applied Physics, 1988, 27, 169-179.	1.5	353
3	Microscopic thickness determination of thin graphite films formed on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>SiC</mml:mi></mml:mrow></mml:math>from quantized oscillation in reflectivity of low-energy electrons. Physical Review B, 2008, 77, .	3.2	330
4	Coherent phonon manipulation in coupled mechanical resonators. Nature Physics, 2013, 9, 480-484.	16.7	274
5	Bit storage and bit flip operations in an electromechanical oscillator. Nature Nanotechnology, 2008, 3, 275-279.	31.5	269
6	Motion detection of a micromechanical resonator embedded in a d.c. SQUID. Nature Physics, 2008, 4, 785-788.	16.7	166
7	Growth process of IIIâ€“V compound semiconductors by migration-enhanced epitaxy. Journal of Crystal Growth, 1990, 105, 326-338.	1.5	151
8	Interconnect-free parallel logic circuits in a single mechanical resonator. Nature Communications, 2011, 2, 198.	12.8	140
9	Atomic-scale imaging of strain relaxation via misfit dislocations in highly mismatched semiconductor heteroepitaxy: InAs/GaAs(111)A. Physical Review B, 1997, 55, 1337-1340.	3.2	136
10	Phonon-cavity electromechanics. Nature Physics, 2012, 8, 387-392.	16.7	127
11	Phonon Lasing in an Electromechanical Resonator. Physical Review Letters, 2013, 110, 127202.	7.8	127
12	Imaging of Friedel Oscillation Patterns of Two-Dimensionally Accumulated Electrons at Epitaxially Grown InAs(111)ASurfaces. Physical Review Letters, 2001, 86, 3384-3387.	7.8	122
13	Inhibitions of three dimensional island formation in InAs films grown on GaAs (111)A surface by molecular beam epitaxy. Applied Physics Letters, 1996, 69, 776-778.	3.3	121
14	Phonon waveguides for electromechanical circuits. Nature Nanotechnology, 2014, 9, 520-524.	31.5	118
15	A strict experimental test of macroscopic realism in a superconducting flux qubit. Nature Communications, 2016, 7, 13253.	12.8	105
16	Surface structure transitions on InAs and GaAs (001) surfaces. Physical Review B, 1995, 51, 9836-9854.	3.2	98
17	Conductance modulation by individual acceptors in Si nanoscale field-effect transistors. Applied Physics Letters, 2007, 90, 102106.	3.3	90
18	Stacking domains of epitaxial few-layer graphene on SiC(0001). Physical Review B, 2009, 80, .	3.2	84

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19	A Scanning Tunneling Microscopy-Reflection High Energy Electron Diffraction-Rate Equation Study of the Molecular Beam Epitaxial Growth of InAs on GaAs(001), (110) and (111)Aâ€“Quantum Dots and Two-Dimensional Modes. Japanese Journal of Applied Physics, 1997, 36, 4111-4117.	1.5	83
20	Controllable coupling between flux qubit and nanomechanical resonator by magnetic field. New Journal of Physics, 2007, 9, 35-35.	2.9	75
21	An electromechanical Ising Hamiltonian. Science Advances, 2016, 2, e1600236.	10.3	73
22	Two-Mode Thermal-Noise Squeezing in an Electromechanical Resonator. Physical Review Letters, 2014, 113, 167203.	7.8	67
23	Theoretical Study of Epitaxial Graphene Growth on SiC(0001) Surfaces. Applied Physics Express, 0, 2, 065502.	2.4	62
24	A multimode electromechanical parametric resonator array. Scientific Reports, 2014, 4, 4448.	3.3	62
25	Observation of Collective Coupling between an Engineered Ensemble of Macroscopic Artificial Atoms and a Superconducting Resonator. Physical Review Letters, 2016, 117, 210503.	7.8	62
26	Two-dimensional growth of InSb thin films on GaAs(111)A substrates. Applied Physics Letters, 2000, 76, 589-591.	3.3	61
27	Replacement of groupâ€III atoms on the growing surface during migrationâ€enhanced epitaxy. Journal of Applied Physics, 1990, 68, 1610-1615.	2.5	60
28	Vibration Amplification, Damping, and Self-Oscillations in Micromechanical Resonators Induced by Optomechanical Coupling through Carrier Excitation. Physical Review Letters, 2011, 106, 036801.	7.8	51
29	Photoluminescence characteristics of AlGaAsâ€GaAs single quantum wells grown by migrationâ€enhanced epitaxy at 300â€‰Â°C substrate temperature. Applied Physics Letters, 1987, 50, 1686-1687.	3.3	49
30	Gate-controlled electromechanical backaction induced by a quantum dot. Nature Communications, 2016, 7, 11132.	12.8	47
31	GaAs-based micro/nanomechanical resonators. Semiconductor Science and Technology, 2017, 32, 103003.	2.0	47
32	Thickness Determination of Graphene Layers Formed on SiC Using Low-Energy Electron Microscopy. E-Journal of Surface Science and Nanotechnology, 2008, 6, 107-110.	0.4	46
33	On-chip temporal focusing of elastic waves in a phononic crystal waveguide. Nature Communications, 2018, 9, 1331.	12.8	46
34	Step-Flow Growth on Vicinal GaAs Surfaces by Migration-Enhanced Epitaxy. Japanese Journal of Applied Physics, 1989, 28, L1456-L1459.	1.5	44
35	Piezoelectrically pumped parametric amplification and Q enhancement in an electromechanical oscillator. Applied Physics Letters, 2008, 92, 173109.	3.3	44
36	Proposed Robust Entanglement-Based Magnetic Field Sensor Beyond the Standard Quantum Limit. Physical Review Letters, 2015, 115, 170801.	7.8	44

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37	Local Density of States in Zero-Dimensional Semiconductor Structures. Physical Review Letters, 2001, 87, 196804.	7.8	43
38	Dispersive and Dissipative Coupling in a Micromechanical Resonator Embedded with a Nanomechanical Resonator. Nano Letters, 2015, 15, 2312-2317.	9.1	43
39	Local conductance measurements of double-layer graphene on SiC substrate. Nanotechnology, 2009, 20, 445704.	2.6	38
40	An electromechanical membrane resonator. Applied Physics Letters, 2012, 101, 063102.	3.3	38
41	Optically detected magnetic resonance of high-density ensemble of NV^{â^'}centers in diamond. Journal of Physics Condensed Matter, 2016, 28, 275302.	1.8	38
42	Single-Turn GaAs/InAs Nanotubes Fabricated Using the Supercritical CO2Drying Technique. Japanese Journal of Applied Physics, 2003, 42, L791-L794.	1.5	37
43	Influence of monomolecular steps on the first-order structure transition of an InAs(001) surface. Physical Review Letters, 1993, 70, 1299-1302.	7.8	36
44	Optical Tuning of Coupled Micromechanical Resonators. Applied Physics Express, 0, 2, 062202.	2.4	36
45	Unified Model for Structure Transition and Electrical Properties of InAs (001) Surfaces Studied by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 1994, 33, L1423-L1426.	1.5	35
46	Extremely long surface diffusion of Ga and critical nucleation on As-rich GaAs(001) surfaces caused by phase transitions. Physical Review B, 1997, 56, 12080-12083.	3.2	35
47	Thickness-dependent electron accumulation in InAs thin films onGaAs(111)A:â€ƒA scanning-tunneling-spectroscopy study. Physical Review B, 1998, 58, R4219-R4222.	3.2	35
48	Improved resonance characteristics of GaAs beam resonators by epitaxially induced strain. Applied Physics Letters, 2008, 92, 251913.	3.3	35
49	Limit cycles and bifurcations in a nonlinear MEMS resonator with a 1:3 internal resonance. Applied Physics Letters, 2019, 114, .	3.3	34
50	High-sensitivity charge detection using antisymmetric vibration in coupled micromechanical oscillators. Applied Physics Letters, 2011, 98, .	3.3	33
51	Multi-mode parametric coupling in an electromechanical resonator. Applied Physics Letters, 2013, 103, .	3.3	32
52	Entangled-state generation and Bell inequality violations in nanomechanical resonators. Physical Review B, 2014, 90, .	3.2	32
53	A phonon transistor in an electromechanical resonator array. Applied Physics Letters, 2013, 102, .	3.3	31
54	Single-Electron-Resolution Electrometer Based on Field-Effect Transistor. Japanese Journal of Applied Physics, 2008, 47, 8305-8310.	1.5	30

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55	Twoâ€Dimensional Patterning of Flexible Designs with High Halfâ€Pitch Resolution by Using Block Copolymer Lithography. Advanced Materials, 2008, 20, 1684-1689.	21.0	29
56	Microelectromechanical displacement sensing using InAs/AlGaSb heterostructures. Applied Physics Letters, 2003, 82, 394-396.	3.3	28
57	Cooling of a micro-mechanical resonator by the back-action of Lorentz force. New Journal of Physics, 2008, 10, 043015.	2.9	28
58	Spin dynamics of two-dimensional electrons in a quantum Hall system probed by time-resolved Kerr rotation spectroscopy. Physical Review B, 2008, 78, .	3.2	28
59	Tunable Backaction of a DC SQUID on an Integrated Micromechanical Resonator. Physical Review Letters, 2010, 105, 207203.	7.8	28
60	Graphene-Based Nano-Electro-Mechanical Switch with High On/Off Ratio. Applied Physics Express, 2013, 6, 055101.	2.4	28
61	Direct comparison of GaAs surface morphology between migration enhanced epitaxy and molecular beam epitaxy using in situ scanning electron microscopy. Applied Physics Letters, 1996, 68, 63-65.	3.3	27
62	Excellent electric properties of free-standing InAs membranes. Applied Physics Letters, 2001, 78, 2372-2374.	3.3	27
63	Hopf and period-doubling bifurcations in an electromechanical resonator. Applied Physics Letters, 2016, 109, .	3.3	26
64	Electrostatically Induced Phononic Crystal. Physical Review Applied, 2019, 11, .	3.8	26
65	Parametrically pumped ultrahigh Q electromechanical resonator. Applied Physics Letters, 2008, 92, 253109.	3.3	25
66	Quantum point contact displacement transducer for a mechanical resonator at sub-Kelvin temperatures. Applied Physics Letters, 2013, 103, 192105.	3.3	24
67	Improving the lifetime of the nitrogen-vacancy-center ensemble coupled with a superconducting flux qubit by applying magnetic fields. Physical Review A, 2015, 91, .	2.5	24
68	Cavity-less on-chip optomechanics using excitonic transitions in semiconductor heterostructures. Nature Communications, 2015, 6, 8478.	12.8	24
69	Electron paramagnetic resonance spectroscopy using a single artificial atom. Communications Physics, 2019, 2, .	5.3	24
70	On-Chip Coherent Transduction between Magnons and Acoustic Phonons in Cavity Magnomechanics. Physical Review Applied, 2022, 17, .	3.8	24
71	First-order surface-structure transition on the (001) InAs surface studied with improved high-energy electron reflectivity measurements. Physical Review B, 1992, 45, 1511-1513.	3.2	23
72	Scanning tunneling microscopy observation of monolayer steps on GaAs(001) vicinal surfaces grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1993, 63, 678-680.	3.3	23

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73	From ferro- to antiferromagnetism via exchange-striction of MnAs/GaAs(001). Europhysics Letters, 2005, 72, 479-485.	2.0	23
74	A $delta$-Doped InGaP/InGaAs pHEMT With Different Doping Profiles for Device-Linearity Improvement. IEEE Transactions on Electron Devices, 2007, 54, 1617-1625.	3.0	23
75	Improving the Coherence Time of a Quantum System via a Coupling to a Short-Lived System. Physical Review Letters, 2015, 114, 120501.	7.8	23
76	A strongly coupled Î›-type micromechanical system. Applied Physics Letters, 2016, 108, .	3.3	23
77	Step motion and As desorption on InAs(001) surfaces observed by scanning tunneling microscopy. Physical Review B, 1993, 48, 2807-2810.	3.2	22
78	Imaging of layer by layer growth processes during molecular beam epitaxy of GaAs on (111)A substrates by scanning electron microscopy. Applied Physics Letters, 1998, 73, 3079-3081.	3.3	22
79	In-plane conductance measurement of graphene nanoislands using an integrated nanogap probe. Nanotechnology, 2008, 19, 495701.	2.6	22
80	Wide-band idler generation in a GaAs electromechanical resonator. Physical Review B, 2011, 84, .	3.2	22
81	Parametric mode mixing in asymmetric doubly clamped beam resonators. New Journal of Physics, 2013, 15, 015023.	2.9	22
82	Rapid switching in high-Q mechanical resonators. Applied Physics Letters, 2014, 105, .	3.3	22
83	Surface Migration of Ga and Al Atoms on (100) GaAs and AlAs during Migration-Enhanced Epitaxy. Japanese Journal of Applied Physics, 1989, 28, 1307-1311.	1.5	21
84	Scanning tunneling microscopy studies of strain relaxation and misfit dislocations in InAs layers grown on GaAs(110) and GaAs(111)A. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1997, 15, 915-918.	2.1	21
85	Electron-Spin Manipulation and Resonator Readout in a Double-Quantum-Dot Nanoelectromechanical System. Physical Review Letters, 2008, 100, 136802.	7.8	21
86	Coherent Control of Micro/Nanomechanical Oscillation Using Parametric Mode Mixing. Applied Physics Express, 2012, 5, 014001.	2.4	21
87	Electron paramagnetic resonance spectroscopy using a direct current-SQUID magnetometer directly coupled to an electron spin ensemble. Applied Physics Letters, 2016, 108, 052601.	3.3	21
88	Influence of an As-Free Atmosphere in Migration-Enhanced Epitaxy on Step-Flow Growth. Japanese Journal of Applied Physics, 1991, 30, 802-808.	1.5	20
89	Growth of very-high-mobility AlGaSbâˆ•InAs high-electron-mobility transistor structure on si substrate for high speed electronic applications. Applied Physics Letters, 2007, 90, 023509.	3.3	20
90	Contact Conductance Measurement of Locally Suspended Graphene on SiC. Applied Physics Express, 2010, 3, 045101.	2.4	20

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91	Single-crystalline 4H-SiC micro cantilevers with a high quality factor. Sensors and Actuators A: Physical, 2013, 197, 122-125.	4.1	20
92	Growth of GaAs/ErAs/GaAs structures by migrationâ€enhanced epitaxy. Applied Physics Letters, 1992, 60, 2341-2343.	3.3	18
93	Drastic Improvement in Surface Flatness Properties by Using GaAs (111)A Substrates in Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1999, 38, 635-644.	1.5	18
94	Enhanced force sensitivity and noise squeezing in an electromechanical resonator coupled to a nanotransistor. Applied Physics Letters, 2010, 97, 253105.	3.3	18
95	Demonstration of Multiple Internal Resonances in a Microelectromechanical Self-Sustained Oscillator. Physical Review Applied, 2020, 13, .	3.8	18
96	Influence of surface reconstruction on the As desorption process from a (001) GaAs surface evaluated by improved high-energy electron-reflectivity measurements. Physical Review B, 1991, 44, 5897-5900.	3.2	17
97	Flattening Transition on GaAs (411)A Surfaces Observed by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 1995, 34, L1490-L1493.	1.5	17
98	Surface-defect formation on heavily doped InAs and GaAs layers studied by scanning tunneling microscopy. Physical Review B, 1996, 53, 4565-4569.	3.2	17
99	Improvement in the Electrical Properties of GaAs/InAs/GaAs Structures through the Use of (111)A Substrates. Japanese Journal of Applied Physics, 1998, 37, 1599-1602.	1.5	17
100	Infrared detection with silicon nano-field-effect transistors. Applied Physics Letters, 2007, 90, 223108.	3.3	17
101	Tuneable electromechanical comb generation. Applied Physics Letters, 2012, 100, .	3.3	17
102	Self-sustained oscillations of a torsional SQUID resonator induced by Lorentz-force back-action. Nature Communications, 2013, 4, 1803.	12.8	17
103	Phonon propagation dynamics in band-engineered one-dimensional phononic crystal waveguides. New Journal of Physics, 2015, 17, 113032.	2.9	17
104	Quantum Interference Effects in the Magnetopiezoresistance ofInAs/AlGaSbQuasi-One-Dimensional Electron Systems. Physical Review Letters, 2004, 93, 036603.	7.8	16
105	Force/displacement detection using quantum transport in InAsâˆ•AlGaSb two-dimensional heterostructures. Applied Physics Letters, 2005, 86, 052106.	3.3	16
106	Device linearity comparison of uniformly doped and /spl delta/-doped In/sub 0.52/Al/sub 0.48/As/In/sub 0.6/Ga/sub 0.4/As metamorphic HEMTs. IEEE Electron Device Letters, 2006, 27, 535-537.	3.9	16
107	Stability and reactivity of steps in the initial stage of graphene growth on the SiC(0001) surface. Physical Review B, 2013, 88, .	3.2	16
108	Dynamic Control of the Coupling between Dark and Bright Excitons with Vibrational Strain. Physical Review Letters, 2018, 120, 267401.	7.8	16

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109	Real-Space Characterization of Cavity-Coupled Waveguide Systems in Hypersonic Phononic Crystals. Physical Review Applied, 2020, 13, .	3.8	16
110	As desorption from GaAs and AlAs surfaces studied by improved highâ€energy electron reflectivity measurements. Journal of Applied Physics, 1992, 71, 1753-1759.	2.5	15
111	Dependence of ErAs Clustering and Er Segregation in ErAs/GaAs Heterostructures on Growth Temperature. Japanese Journal of Applied Physics, 1993, 32, L1784-L1787.	1.5	15
112	Step Motion and Structure Transition on InAs and GaAs (001) Surfaces Observed by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 1994, 33, 716-720.	1.5	15
113	Impurity conduction in phosphorus-doped buried-channel silicon-on-insulator field-effect transistors at temperatures between 10 and295K. Physical Review B, 2006, 74, .	3.2	15
114	Room temperature piezoelectric displacement detection via a silicon field effect transistor. Applied Physics Letters, 2009, 95, .	3.3	15
115	A symmetry-breaking electromechanical detector. Applied Physics Letters, 2010, 96, .	3.3	15
116	Ultrahigh-QMicromechanical Resonators by Using Epitaxially Induced Tensile Strain in GaNAs. Applied Physics Express, 2013, 6, 111201.	2.4	15
117	Mechanical random access memory in a phonon circuit. Applied Physics Express, 2014, 7, 125201.	2.4	15
118	Broadband reconfigurable logic gates in phonon waveguides. Scientific Reports, 2017, 7, 12745.	3.3	15
119	Mechanical Kerr Nonlinearity of Wave Propagation in an On-Chip Nanoelectromechanical Waveguide. Physical Review Applied, 2020, 13, .	3.8	15
120	Impact-parameter dependent stopping powers for axially channeled and semichanneled MeV He ions in GaAs:Er. Physical Review B, 1994, 49, 14387-14396.	3.2	14
121	Fabrication of conductive single-crystal semiconductor nanoscale electromechanical structures. Applied Physics Letters, 2002, 80, 4428-4430.	3.3	14
122	First principles and macroscopic theories of semiconductor epitaxial growth. Journal of Crystal Growth, 2002, 237-239, 206-211.	1.5	14
123	Resist-Pattern Guided Self-assembly of Symmetric Diblock Copolymer. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2006, 19, 385-388.	0.3	14
124	Discrete-time quadrature feedback cooling of a radio-frequency mechanical resonator. Applied Physics Letters, 2011, 99, .	3.3	14
125	Energy Dissipation in Graphene Mechanical Resonators with and without Free Edges. Micromachines, 2016, 7, 158.	2.9	14
126	Electron paramagnetic resonance spectroscopy of Er3+:Y2SiO5 using a Josephson bifurcation amplifier: Observation of hyperfine and quadrupole structures. Physical Review Materials, 2018, 2, .	2.4	14

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127	Proposal of Carbon Nanotube Inductors. Journal of Physics: Conference Series, 2006, 38, 49-52.	0.4	13
128	Three-dimensional alignment with 10nm order accuracy in electron-beam lithography on rotated sample for three-dimensional nanofabrication. Journal of Vacuum Science & Technology B, 2008, 26, 2529-2533.	1.3	13
129	Epitaxial Trilayer Graphene Mechanical Resonators Obtained by Electrochemical Etching Combined with Hydrogen Intercalation. Japanese Journal of Applied Physics, 2013, 52, 04CH01.	1.5	13
130	Energy dissipation in edged and edgeless graphene mechanical resonators. Journal of Applied Physics, 2014, 116, 064304.	2.5	13
131	Dynamical coupling between a nuclear spin ensemble and electromechanical phonons. Nature Communications, 2018, 9, 2993.	12.8	13
132	An opto-electro-mechanical system based on evanescently-coupled optical microbottle and electromechanical resonator. Applied Physics Letters, 2018, 112, .	3.3	13
133	Rare-Earth-Mediated Optomechanical System in the Reversed Dissipation Regime. Physical Review Letters, 2021, 126, 047404.	7.8	13
134	Superfield perturbation theory in harmonic superspace. Physical Review D, 1985, 32, 1954-1967.	4.7	12
135	Structural analysis of erbium sheetâ€doped GaAs grown by molecularâ€beam epitaxy, with ion channeling followed by Monte Carlo simulation. Journal of Applied Physics, 1995, 77, 3095-3103.	2.5	12
136	Magnetoelastic coupling ofMnAsâ•GaAs(001)close to the phase transition. Physical Review B, 2004, 70, .	3.2	12
137	Thermoelastic damping in GaAs micromechanical resonators. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2920-2922.	0.8	12
138	Superconductivity in Tungsten-Carbide Nanowires Deposited from the Mixtures of W(CO)₆and C₁₄H₁₀. Japanese Journal of Applied Physics, 2013, 52, 075001.	1.5	12
139	Phonon-bottlenecked spin relaxation of Er³⁺:Y₂SiO₅at sub-kelvin temperatures. Applied Physics Express, 2018, 11, 043002.	2.4	12
140	Virtual Exceptional Points in an Electromechanical System. Physical Review Applied, 2019, 11, .	3.8	12
141	Generic Rotating-Frame-Based Approach to Chaos Generation in Nonlinear Micro- and Nanoelectromechanical System Resonators. Physical Review Letters, 2020, 125, 174301.	7.8	12
142	N = 2 harmonic superspace with central charges and its application to self-interacting massive hypermultiplets. Annals of Physics, 1986, 172, 26-39.	2.8	11
143	Electronic properties of monolayer steps on (2Ã—4)/c(2Ã—8) reconstructed GaAs(001) surfaces. Physical Review B, 1996, 54, 4428-4431.	3.2	11
144	Microscopic investigation of the surface phase transition on GaAs(001) surfaces. Surface Science, 1999, 433-435, 382-386.	1.9	11

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145	Magneto-optical spectroscopy of excitons and trions in charge-tunable quantum dots. Physical Review B, 2009, 79, .	3.2	11
146	Anomalous Distribution of In Atoms in GaAs during Migration-Enhanced Epitaxy. Japanese Journal of Applied Physics, 1989, 28, L2010-L2012.	1.5	10
147	First-principles calculation for misfit dislocations in InAs/GaAs(110) heteroepitaxy. Surface Science, 1999, 433-435, 900-903.	1.9	10
148	Nanogap electrodes on Si cantilever for local conductance measurement. Journal of Physics: Conference Series, 2007, 61, 856-860.	0.4	10
149	Flexible Nanofabrication in Three-Dimensional Electron-Beam Lithography Enhanced by Suppression of Proximity Effect. Applied Physics Express, 0, 1, 097001.	2.4	10
150	Spatial and temporal modulation of exciton photoluminescence properties in GaAs/AlAs dynamic quantum dots formed by surface acoustic waves. Physical Review B, 2009, 80, .	3.2	10
151	Atomic Structure and Physical Properties of Epitaxial Graphene Islands Embedded in SiC(0001) Surfaces. Applied Physics Express, 2010, 3, 115103.	2.4	10
152	Optomechanical photoabsorption spectroscopy of exciton states in GaAs. Applied Physics Letters, 2012, 101, 082107.	3.3	10
153	Feedback control of multiple mechanical modes in coupled micromechanical resonators. Applied Physics Letters, 2017, 110, 053106.	3.3	10
154	Migration-enhanced epitaxy. Applied Surface Science, 1988, 33-34, 406-412.	6.1	9
155	Ferromagnetic-induced component in piezoresistance of GaMnAs. Physical Review B, 2013, 87, .	3.2	9
156	Wide-bandwidth charge sensitivity with a radio-frequency field-effect transistor. Applied Physics Letters, 2013, 103, 143102.	3.3	9
157	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. Japanese Journal of Applied Physics, 2011, 50, 070115.	1.5	9
158	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. Japanese Journal of Applied Physics, 2011, 50, 095601.	1.5	9
159	First-principles calculations on atomic and electronic structures of misfit dislocations in InAs/GaAs(110) and GaAs/InAs(110) heteroepitaxies. Journal of Crystal Growth, 1999, 201-202, 256-259.	1.5	8
160	Electron and Hole Proximity Effects in the InAs/AlSb/GaSb System. Japanese Journal of Applied Physics, 2000, 39, 2448-2451.	1.5	8
161	InAs/AlGaSb heterostructure displacement sensors for MEMS/NEMS applications. Journal of Crystal Growth, 2003, 251, 556-559.	1.5	8
162	Perpendicular magnetic fields in cantilever beam magnetometry. Journal of Applied Physics, 2004, 96, 2773-2778.	2.5	8

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163	Carbon Multiprobe on a Si Cantilever for Pseudo-Metalâ€“Oxideâ€“Semiconductor Field-Effect-Transistor. Japanese Journal of Applied Physics, 2006, 45, 2009-2013.	1.5	8
164	Photoluminescence Dynamics of GaAs/AlAs Quantum Wells Modulated by Surface Acoustic Waves. Japanese Journal of Applied Physics, 2007, 46, L758-L760.	1.5	8
165	Local conductance measurement of few-layer graphene on SiC substrate using an integrated nanogap probe. Journal of Physics: Conference Series, 2008, 100, 052006.	0.4	8
166	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. Japanese Journal of Applied Physics, 2011, 50, 070115.	1.5	8
167	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. Japanese Journal of Applied Physics, 2011, 50, 095601.	1.5	8
168	Motion detection of a micromechanical cantilever through magneto-piezovoltage in two-dimensional electron systems. Applied Physics Letters, 2012, 100, 012106.	3.3	8
169	Observing the semiconducting band-gap alignment of MoS2 layers of different atomic thicknesses using a MoS2/SiO2/Si heterojunction tunnel diode. Applied Physics Letters, 2015, 107, .	3.3	8
170	Enhanced visibility of two-mode thermal squeezed states via degenerate parametric amplification and resonance. New Journal of Physics, 2016, 18, 083009.	2.9	8
171	Resist Coating on Vertical Side Faces Using Conventional Spin Coating for Creating Three-Dimensional Nanostructures in Semiconductors. Applied Physics Express, 2010, 3, 106501.	2.4	8
172	Phase transition on III-V compound semiconductor surfaces observed by an improved RHEED technique. Journal of Crystal Growth, 1993, 127, 976-980.	1.5	7
173	Direct determination of impact-parameter-dependent stopping powers for million-electron-volt He ions penetrating Er-doped GaAs. Physical Review A, 1996, 53, 1644-1652.	2.5	7
174	Imaging of Local Charge Density in an InAs/GaAs Two-Dimensional Heterostructure by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 1998, 37, L899-L901.	1.5	7
175	Fabrication and elastic properties of InAs freestanding structures based on InAs/GaAs(111)A heteroepitaxial systems. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1163-1167.	2.7	7
176	InAs/GaAs (111)A heteroepitaxial systems. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 23, 285-292.	2.7	7
177	Strongly Enhanced Sensitivity of Piezoresistive Cantilevers by Utilizing the Superconducting Proximity Effect. Japanese Journal of Applied Physics, 2005, 44, L893-L895.	1.5	7
178	Electron phase modulation in a suspended InAsâˆ•AlGaSb nanomechanical beam. Applied Physics Letters, 2006, 89, 192106.	3.3	7
179	Giant Magneto-Piezoresistance and Internal Friction in a Two-Dimensional Electron System. Japanese Journal of Applied Physics, 2007, 46, L658-L660.	1.5	7
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